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p-type doping of MoS₂ thin films using Nb

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#	Paper	IF	Citations
253	Growth and electrical characterization of two-dimensional layered MoS ₂ /SiC heterojunctions. <i>Applied Physics Letters</i> , 2014 , 105, 203504	3.4	29
252	Hole mobility enhancement and p -doping in monolayer WSe ₂ by gold decoration. 2014 , 1, 034001		104
251	RKKY interaction and intervalley processes in p-doped transition-metal dichalcogenides. <i>Physical Review B</i> , 2014 , 90,	3.3	17
250	Valley- and spin-switch effects in molybdenum disulfide superconducting spin valve. <i>Physical Review B</i> , 2014 , 90,	3.3	30
249	Doping against the native propensity of MoS ₂ : degenerate hole doping by cation substitution. <i>Nano Letters</i> , 2014 , 14, 6976-82	11.5	468
248	Contact research strategy for emerging molybdenum disulfide and other two-dimensional field-effect transistors. 2014 , 2, 092510		37
247	Enhancing the high rate capability and cycling stability of LiMnO ₂ by coating of solid-state electrolyte LiNbO ₃ . <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 22155-65	9.5	64
246	Demonstration of 2D/3D p-MoS ₂ /n-SiC junction. 2014 ,		
245	Valley- and spin-filter in monolayer MoS ₂ . 2014 , 199, 52-55		13
244	MoS_2 Field-Effect Transistors With Graphene/Metal Heterocontacts. 2014 , 35, 599-601		118
243	Electro-vibrational coupling effects on intrinsic friction in transition metal dichalcogenides. <i>RSC Advances</i> , 2015 , 5, 106809-106818	3.7	13
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- 2 Origin of electrically induced defects in monolayer MoS₂ grown by chemical vapor deposition. **2023**
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- 1 Controllable Switching between Highly Rectifying Schottky and p-n Junctions in an Ionic MoS₂ Device. ○